

Nitrogen Depletion Behavior of High-Nitrogen Oxynitride Films After  
Reoxidation with O<sub>2</sub> and N<sub>2</sub>O treatment

林柏村, 賴瓊惠

Microelectronics Engineering

Engineering

chlai@chu.edu.tw

Abstract

We investigated the nitrogen depletion behavior of high nitrogen oxynitride after O<sub>2</sub> or N<sub>2</sub>O reoxidation in a rapid thermal furnace. We observed that the nitrogen concentration decreased in both cases, and the nitrogen distribution moved toward the SiO<sub>2</sub>/Si interface when under N<sub>2</sub>O reoxidation, however, when under O<sub>2</sub> reoxidation it moved toward the surface of the SiO<sub>2</sub>.

Keyword : oxynitride, rapid thermal oxidation, nitrogen depletion, nitrous oxide, reoxidation